



PTO/SB/08a/b (08-03)  
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Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			<b>Complete if Known</b>		
			Application Number	10/618,824-Conf. #5907	
			Filing Date	July 14, 2003	
			First Named Inventor	Terry L. Gilton	
			Art Unit	N/A 2823	
			Examiner Name	Not Yet Assigned H. Lee	
Sheet	1	of	1	Attorney Docket Number	M4065.1006/P1006-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Lee	AA	US-6,337,266	01/08/2002	Zahorik	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>

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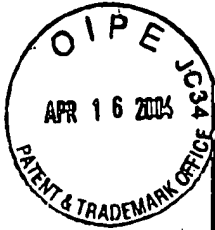
NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

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<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

*Hsin Ming Lee*

*6/16/04*



PTO/SB/08A (10-01)

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Substitute for form 1449A/PTO				<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2623
				Examiner Name	Not Yet Assigned H. Lee
Sheet	1	of	12	Attorney Docket Number	M4065.1006/P1006-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.*	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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	AB	2002/0072188	6/2002	Gilton	
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*Kim Ming Lee* 6/16/04

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				Art Unit	N/A- 2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	2	of	12	Attorney Docket Number	M4065.1006/P1006-A

✓	AS1	4,320,191	3/1982	Yoshikawa et al.	
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*Kevin Ming Lee 6/16/04*

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Kuon Meng Lu 6/16/04

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		Application Number	10/618,824		
		Filing Date	July 14, 2003		
		First Named Inventor	Terry L. Gilton		
		Art Unit	N/A 2823		
		Examiner Name	Not Yet Assigned - H. Lee		
Sheet	4	of	12	Attorney Docket Number	M4065.1006/P1006-A

FOREIGN PATENT DOCUMENTS							
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		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)					
	BA	JP-56126916		10/1981	Akira et al.		
	BB	WO 97/48032		12/18/1997	Kozicki et al.		
	BC	WO 99/28914		06/10/1999	Kozicki et al.		

Examiner Signature	<i>Kevin Mary Lee</i>	Date Considered	8/6/04
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Substitute for form 1449B/PTO		<b>Complete if Known</b>			
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/618,824		
		Filing Date	July 14, 2003		
		First Named Inventor	Terry L. Gilton		
		Group Art Unit	N/A- 2823		
		Examiner Name	Not Yet Assigned H. Lee		
Sheet	5	of	12	Attorney Docket Number	M4065.1006/P1006-A

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T?
Lee	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
*	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
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*	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSbx, Appl. Phys. A 55 (1992) 167-169.	
*	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe <sub>1-x</sub> , Egypt, J. Phys. 17 (1986) 335-342.	
*	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
*	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
*	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
*	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
*	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
*	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
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*	CN	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.	
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*	CQ	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag <sub>2</sub> Se-M, Thin solid films 70 (1980) L1-L4.	
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Kris May Lee 6/16/04

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		Group Art Unit	N/A 2823
		Examiner Name	Not Yet Assigned H. Lee
Sheet	6	of	12
		Attorney Docket Number	M4065.1006/P1006-A

<i>Lee</i>	CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg4I5, Solid State Ionics 70/71 (1994) 72-76.	
*	CX	Boolchand, P., The maximum in glass transition temperature (T <sub>g</sub> ) near x=1/3 in GexSe1-x Glasses, Asian Journal of Physics (2000) 9, 709-72.	
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*	CM1	Chen, G.; Cheng, J.; Chen, W., Effect of Si3N4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
*	CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
*	CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
*	CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
*	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
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*Kevin Ming Lee 6/16/04*

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		Group Art Unit	N/A 2823
		Examiner Name	Not Yet Assigned H. Lee
Sheet	7	of	12
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Lee	CU1	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.
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